L Number	Hits	Search Text	DB	Time stamp
-	39	(("5015502") or ("5648113") or ("5654035") or ("6037003") or	USPAT;	2004/03/17 08:53
		("6319730") or ("6278166") or ("6406960") or ("6420279") or	US-PGPUB,	
		("6407435") or ("5120672") or ("6008091") or ("6171900") or	EPO; JPO;	
		("6309927") or ("6438030") or ("6461905") or ("6573197") or	DERWENT;	
		("5907766") or ("6451657") or ("6451641") or ("6407435")).PN.	IBM_TDB	
-	129	composite near3 dielectric and (high-K high?k (high near2 K))	USPĀT;	2004/03/17 07:16
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	825	(257/310).CCLS.	USPAT;	2004/03/16 18:16
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
_	327	(438/441,746,760).CCLS.	USPAT;	2004/03/16 18:16
-	321	(436/441,740,700 <i>)</i> .CCLS.	US-PGPUB;	2004/03/10 16.10
			EPO; JPO;	
			DERWENT;	
	129	commonity many distorting and think IV hink the hours IV)	IBM_TDB	2004/02/17 07:16
-	129	composite near3 dielectric and (high-K high?k (high near2 K))	USPAT;	2004/03/17 07:16
		°	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	142	composite near3 dielectric and (high-K high?k (high near2 K))	USPAT;	2004/03/17 07:16
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	1944	((multiple multi sub) near3 (film layer)) with (dielectric with (constant	USPAT;	2004/03/17 08:55
		high low standard))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	1
-	521	(((multiple multi sub) near3 (film layer)) with (dielectric with (constant	USPAT;	2004/03/17 08:58
		high low standard))) and ((silicon near2 dioxide) (silicon near2	US-PGPUB:	
		oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	474	((((multiple multi sub) near3 (film layer)) with (dielectric with (constant	USPAT;	2004/03/17 09:02
		high low standard))) and ((silicon near2 dioxide) (silicon near2	US-PGPUB;	
		oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and	ЕРО; ЛРО;	
		((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide)	DERWENT;	
		(barium near2 oxide) (titanium nera2 oxide) PMN PST PZN)	IBM TDB	
	42	(((((multiple multi sub) near3 (film layer)) with (dielectric with	USPAT;	2004/03/17 09:28
		(constant high low standard))) and ((silicon near2 dioxide) (silicon	US-PGPUB:	200 11 05/17 05/20
		near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and	EPO; JPO;	
		((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide)	DERWENT;	
		(barium near2 oxide) (titanium nera2 oxide) PMN PST PZN)) and	IBM_TDB	
		MOSFET	IDM_1DD	
_	0	(((((multiple multi sub) near3 (film layer)) with (dielectric with	TICDAT	2004/02/17 00:20
-	U	(((((multiple multi sub) near3 (film layer)) with (dielectric with (constant high low standard))) and ((silicon near2 dioxide) (silicon	USPAT;	2004/03/17 09:30
			US-PGPUB;	
		near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and	EPO; JPO;	
		((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide)	DERWENT;	
		(barium near2 oxide) (titanium nera2 oxide) PMN PST PZN)) and	IBM_TDB	
	_	((gate near3 dielectic) same (FET EEPROM SONOS))	TIOD A TO	2004/02/27 02 2
-	0	(((((multiple multi sub) near3 (film layer)) with (dielectric with	USPAT;	2004/03/17 09:30
		(constant high low standard))) and ((silicon near2 dioxide) (silicon	US-PGPUB;	
		near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and	ЕРО; ЈРО;	
		((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide)	DERWENT;	
		(barium near2 oxide) (titanium nera2 oxide) PMN PST PZN)) and (gate	IBM_TDB	
		near3 dielectic) and (FET EEPROM SONOS MOSFET)	1	l

-	28	(((((multiple multi sub) near3 (film layer)) with (dielectric with	USPAT;	2004/03/17 09:30
		(constant high low standard))) and ((silicon near2 dioxide) (silicon	US-PGPUB;	
		near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and	ЕРО; ЛРО;	
		((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide)	DERWENT;	
		(barium near2 oxide) (titanium nera2 oxide) PMN PST PZN)) and (gate	IBM_TDB	
		near3 dielectric) and (FET EEPROM SONOS MOSFET)		
-	13	(((((multiple multi sub) near3 (film layer)) with (dielectric with	USPAT;	2004/03/17 10:41
		(constant high low standard))) and ((silicon near2 dioxide) (silicon	US-PGPUB;	
		near2 oxynitride) (silicon near2 nitride) (silicon-rich near3 nitride))) and	ЕРО; ЛРО;	
		((hafnium near2 oxide) (zirconium near2 oxide) (tantalum near2 oxide)	DERWENT;	
		(barium near2 oxide) (titanium nera2 oxide) PMN PST PZN)) and	IBM_TDB	
		((gate near3 dielectric) same (FET EEPROM SONOS))	_	
-	4	(("6013553") or ("6020243")).PN.	USPAT;	2004/03/17 10:16
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM TDB	
_	10016	(257/411,412,382-410,368).CCLS.	USPAT;	2004/03/17 10:47
-	10010	(25/1411,412,302-410,308).CCLS.	US-PGPUB;	2004/03/17 10.47
			EPO; JPO;	
			DERWENT;	
	2027	(429/200 205 216 261 421 501 505) COT 9	IBM_TDB	2004/02/17 10:49
-	3937	(438/300,305,216,261,421,591,595).CCLS.	USPAT;	2004/03/17 10:48
	1		US-PGPUB;	
*			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
-	0	10/656470	USPAT;	2004/03/17 10:48
			US-PGPUB;	
			ЕРО; ЛРО;	
1			DERWENT;	
			IBM_TDB	
-	2	10/051790	USPAT;	2004/03/17 10:56
			US-PGPUB;	
1			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
l <u>-</u>	. 8	2002/0106536	USPĀT;	2004/03/17 10:57
	1		US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
	1		IBM_TDB	
-	8	2002/0106536	USPAT;	2004/03/17 11:01
			US-PGPUB;	
			ЕРО; ЛРО;	
	1		DERWENT;	
	ļ		IBM_TDB	
-	0	(2002/0106536).CCLS.	USPAT;	2004/03/17 10:58
	ľ		US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
	1		IBM_TDB	
_	2	"20020106536"	USPAT;	2004/03/17 11:03
-	2	20020100330	US-PGPUB;	2007/03/11 11.03
	1		ЕРО; ЛРО;	
			DERWENT;	
	_	#20000100211#	IBM_TDB	0004/03/15 11 01
-	2	"20020190311"	USPAT;	2004/03/17 11:04
			US-PGPUB;	
	-		ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	

-	2	"20020115252"	USPAT;	2004/03/17 11:10
			US-PGPUB;	
			ЕРО; ЈРО;	
		•	DERWENT;	
			IBM_TDB	
-	2	"20020142624"	USPAT;	2004/03/17 11:10
			US-PGPUB;	
			ЕРО; ЈРО;	
			DERWENT,	
			IBM_TDB	